



Development of precision tracking detectors at Fermilab

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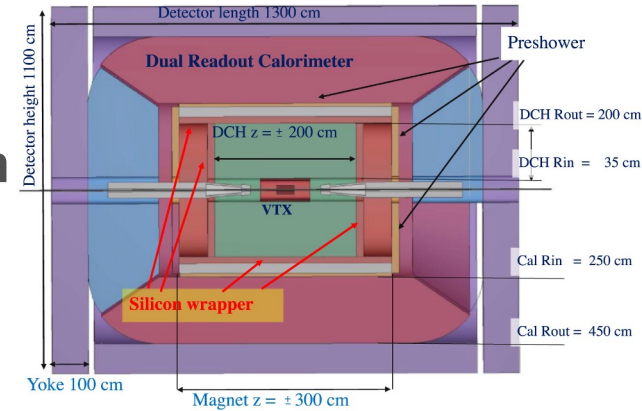
FCC Week 2024

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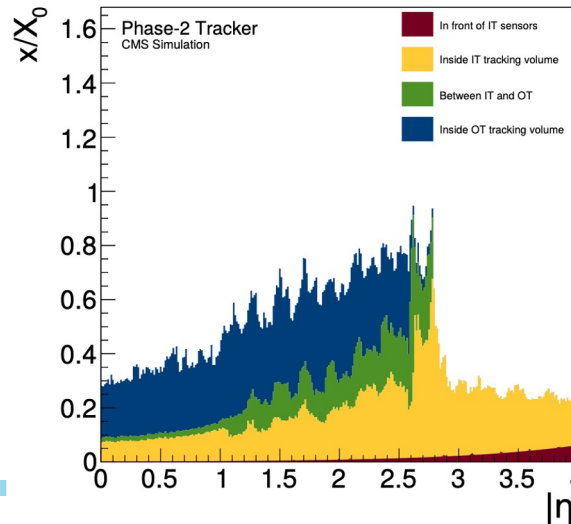
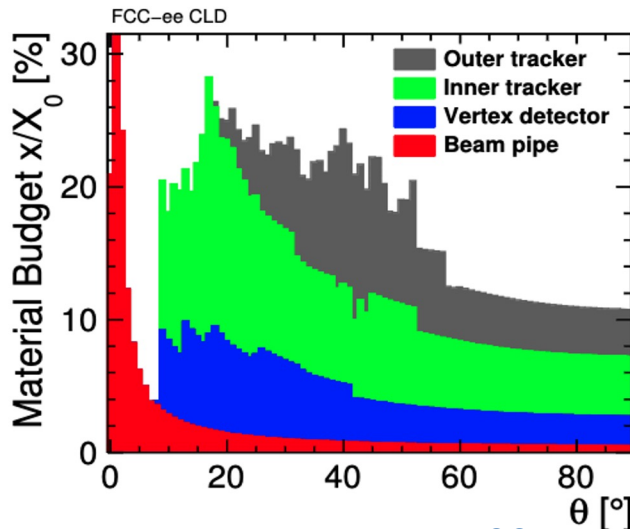
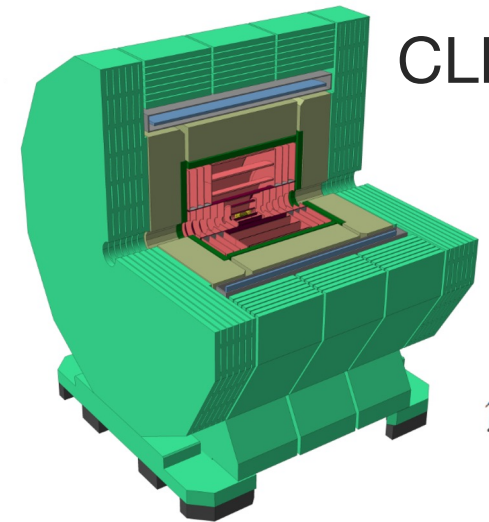
Requirements

- Physics goals
 - Identify b/c quarks and tau leptons from **Higgs**
 - Perform a precise measurements of the **Z boson**
- Require a **5 μm** spatial resolution, angular resolution of **0.1 mrad**
- Very low mass budget
 - First detector layer material budget of 0.2% X_0
 - Total tracking material budget <30% X_0
- Particle ID with time-of-flight

IDEA



CLD



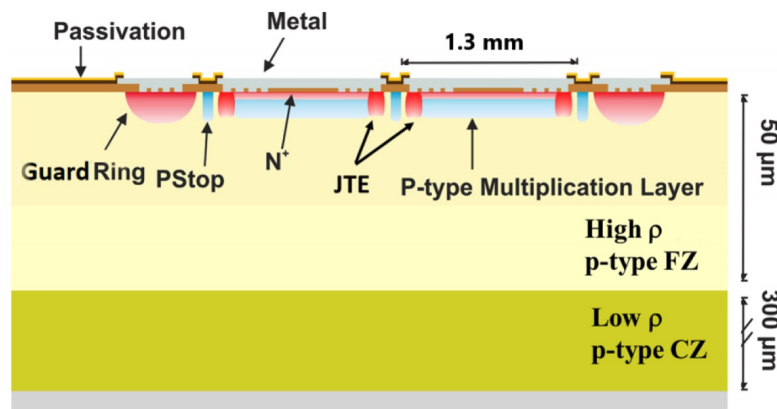
Activities in Fermilab

- Many active directions of R&D ongoing, some highlights:
 - Development of Low-Gain Avalanche Diode sensors and electronics
 - Monolithic Active Pixel Sensors
 - 3D-integrated sensors
 - AI-enabled pixelated sensors

AC-coupled LGADs

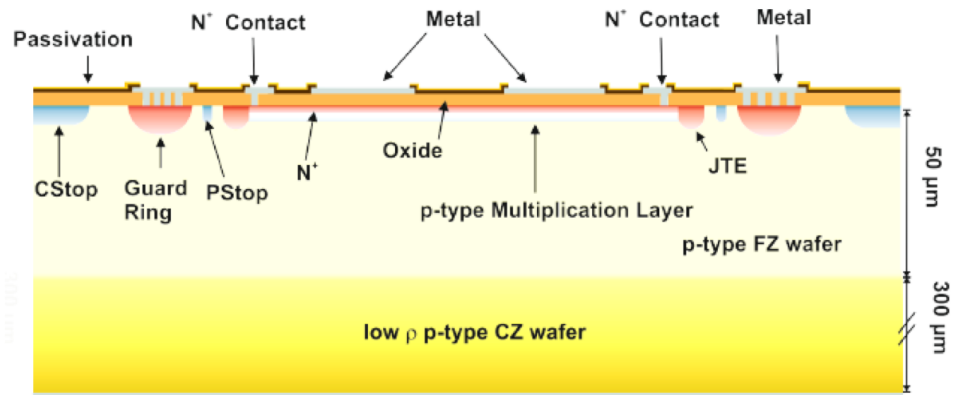
- Improve 4D-trackers to achieve 100% fill factor, and high position resolution
- Active R&D at different manufacturers (FBK, BNL, HPK, etc)
 - 100% fill factor, and fast timing information at a per-pixel level
 - Signal is still generated by drift of multiplied holes into the substrate and AC-coupled through dielectric
 - Electrons collect at the resistive n+ and then slowly flow to an ohmic contact at the edge.

Diagram credit: CNM



DC-LGAD

Metal

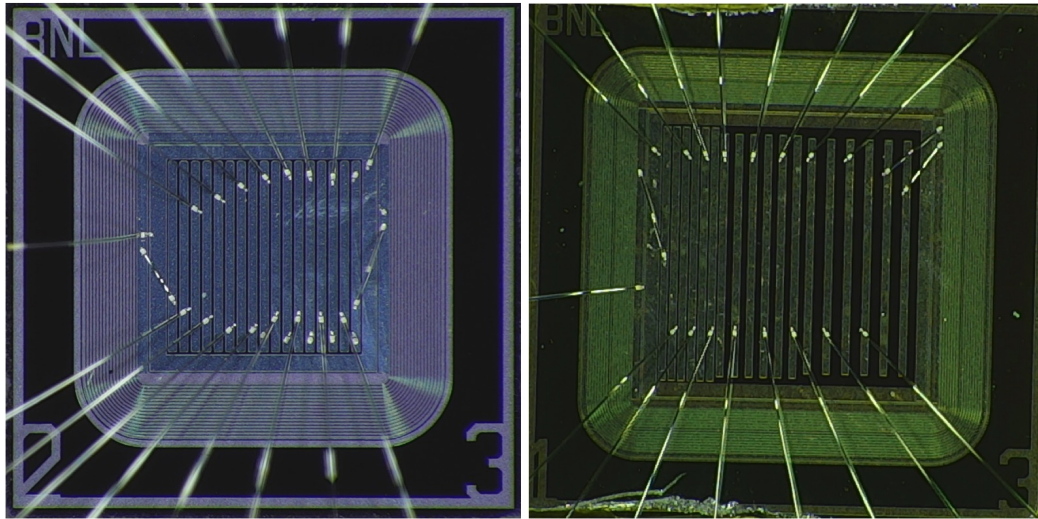


AC-LGAD

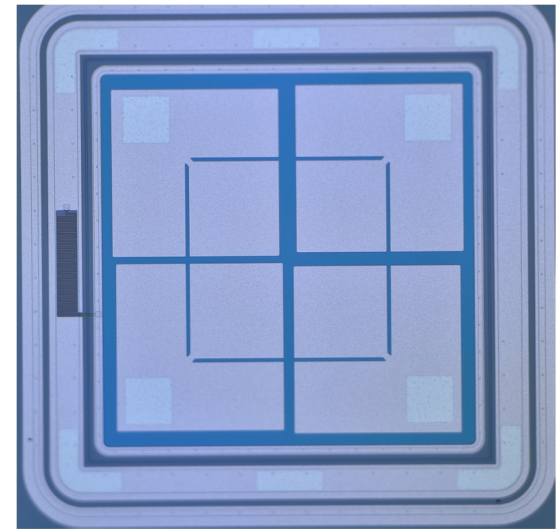
Metal

AC-LGAD sensors prototypes

- An active and highly successful consortium within US-Japan
 - Several rounds manufactured over the last few years
 - R&D from developments for HL-LHC, synergies between HEP and NP
 - Optimize position resolution, timing resolution, fill-factor, ...
- Extensive characterization and design studies
 - Optimize the geometry of readout, and sensor design for performance



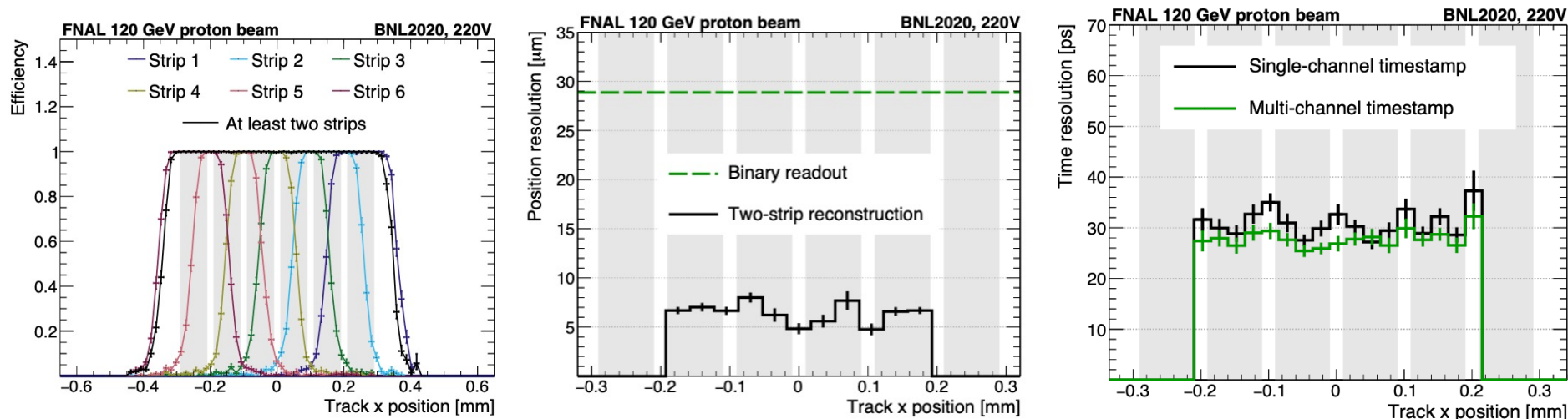
BNL strip AC-LGAD



HPK pads AC-LGAD

Strip-sensor AC-LGADs (short sensors)

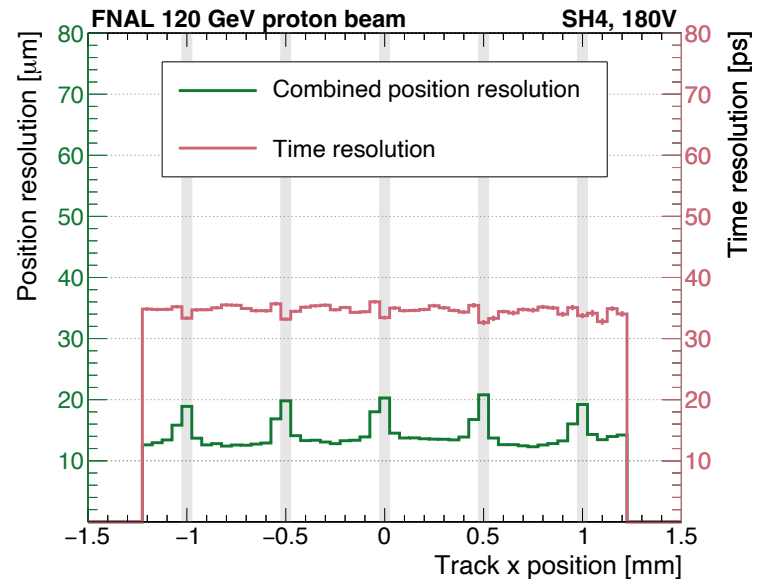
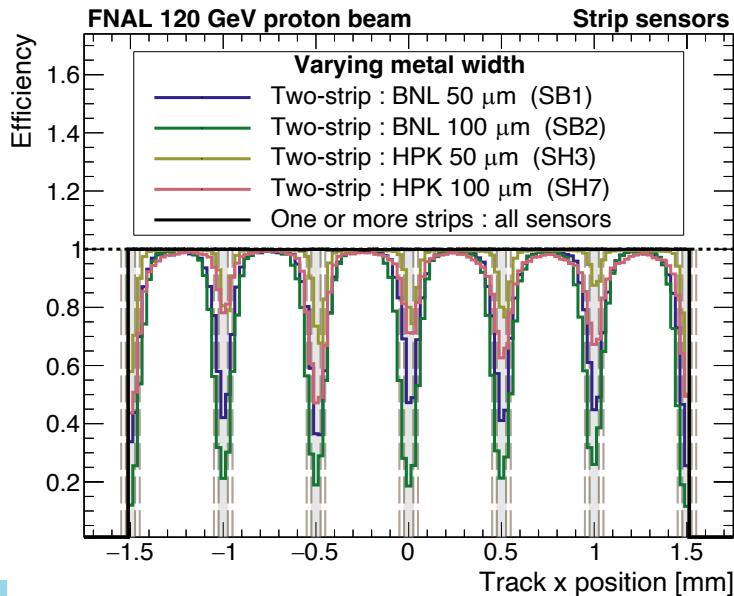
- Excellent performance from several strip prototypes
 - 100% particle detection efficiency across sensor surface
 - Signal shared between neighbors: measure position based on signal ratio
 - Well-tuned signal sharing \rightarrow uniform 5-10 μm resolution



- **First demonstration of simultaneous $\sim 5 \mu\text{m}$, $\sim 30 \text{ ps}$ resolutions in a test beam: technology for 4D-trackers!**

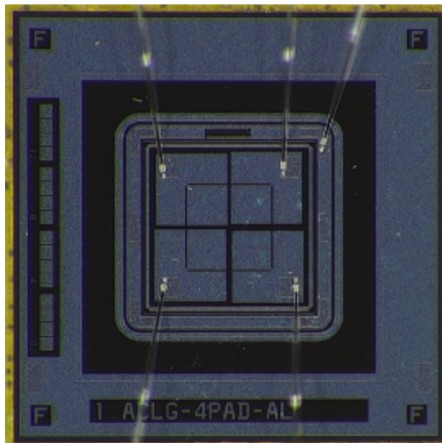
Long AC-LGAD strip sensors performance

- Position reconstruction with ratio of amplitudes
 - Sensor provides 100% efficiency
 - Achieve 15-20 μm resolution in 10 mm strips with 500 μm pitch
- Excellent time
 - Combining 2 channels & correcting for position-dependent delays
 - Achieve 30-35 ps for 10 mm strips

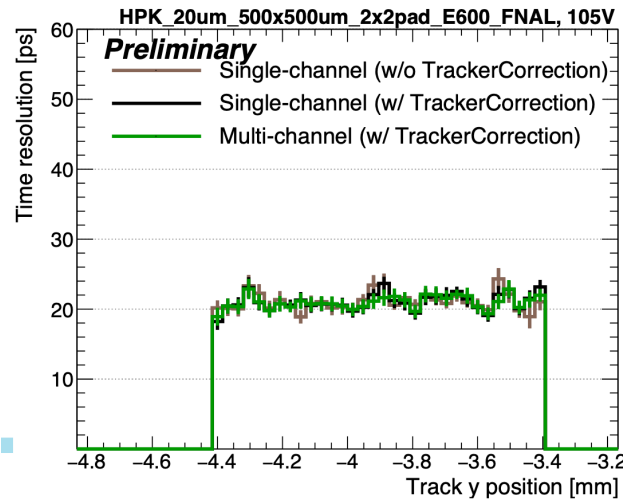


Towards better time resolution

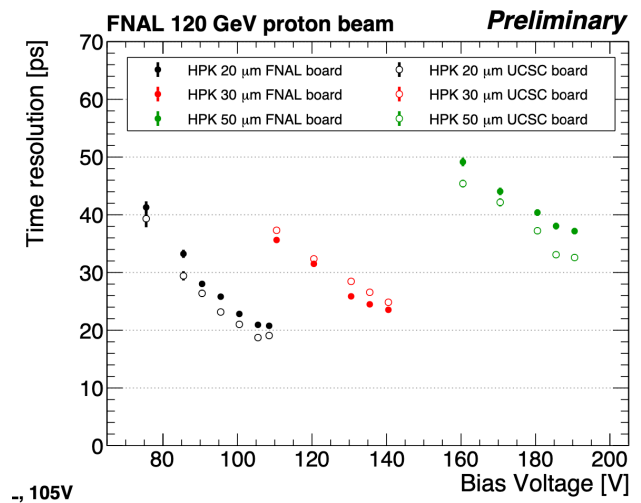
- How do you get better time resolution?
 - Thinner sensors to decrease Landau contribution
- AC-LGAD from HPK with 20, 30, 50 μm thickness
 - Almost fully metallized, optimized for timing performance
- Uniform time resolution across full sensor area
 - 25 ps for 30 μm thick sensor, 20 ps for 20 μm thick sensor



HPK 2x2, 500x500 μm^2 pixel size



20 ps across full sensor surface

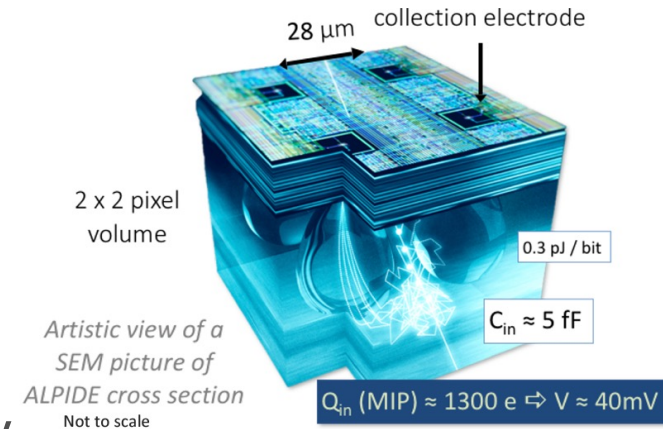


Time resolution for 20, 30 and 50 μm -thick sensors

MAPS design efforts with Skywater

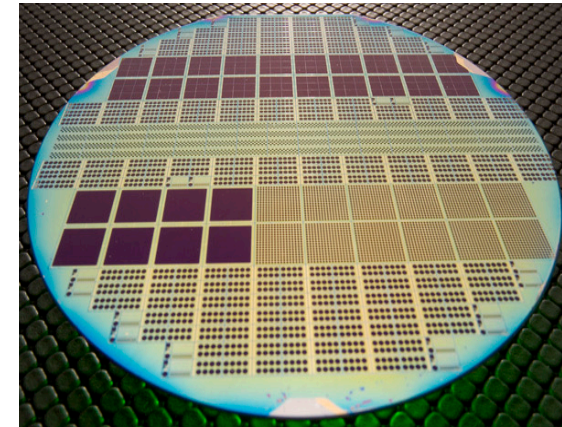
• GOALS

- US manufactured sensor capability for HEP experiments
- Optimize the process towards HEP sensors
- Co-design sensor and readout electronics
- Broad adoption of development in community



• HOW?

- Partner with Skywater Technologies
- Consortium of UC, UIC, UF, Purdue, Cornell, for device simulation and testing
- Engineering run with various designs
- Testing of sensors at Fermilab and partners

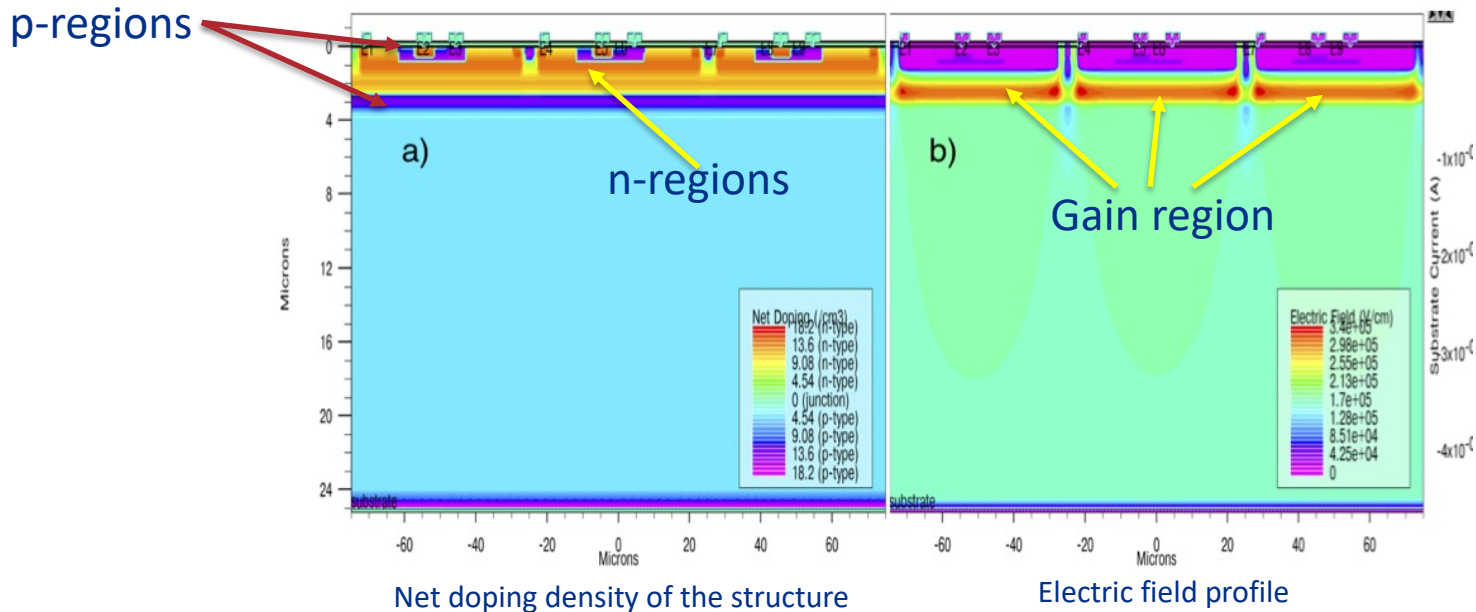


Commercial Partner

- Most **advanced process** among HEP MAPS
 - Fabricated on SkyWater's **90 nm** process
 - Demonstrate domestic production for future HEP experiments
- We will work with SkyWater to modify their standard epitaxial silicon layer
 - Adapt and optimize SkyWater process to develop particle detectors
 - Use thicker, higher-resistivity epitaxy with deep-well implants on a standard CMOS substrate
 - The standard CMOS process flow can then be used to fabricate IC resulting in a monolithic sensor with integrated signal processing

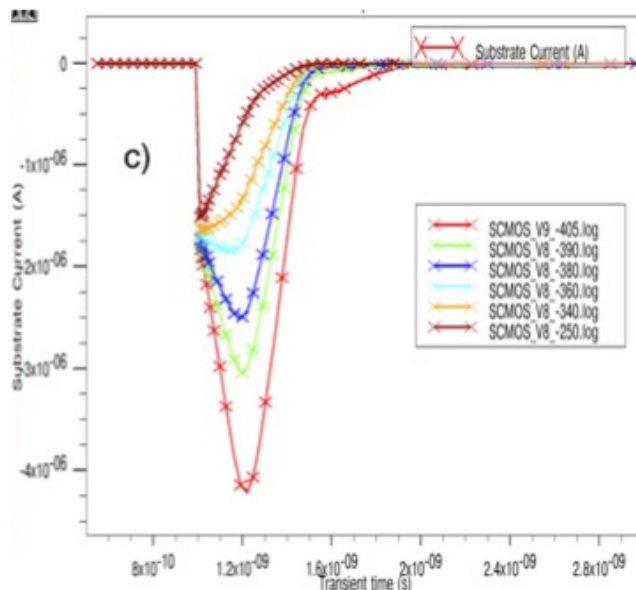
Simulations

- TCAD simulations were used to establish the feasibility of the proposed work, and we started discussions with SkyWater.
 - The initial TCAD studies for SkyWater CMOS are based on our previous work to establish designs for 8" sensor wafer production



Simulations

- Depleted CMOS sensor operation can be limited by the fields in the region of the deep wells causing breakdown or affecting transistor operation.
 - While the SkyWater 90 nm process is not an explicit HV design, it is likely compatible with the fields in fully depleted sensors
 - Can mitigate the fields near the wells with deep n-implant



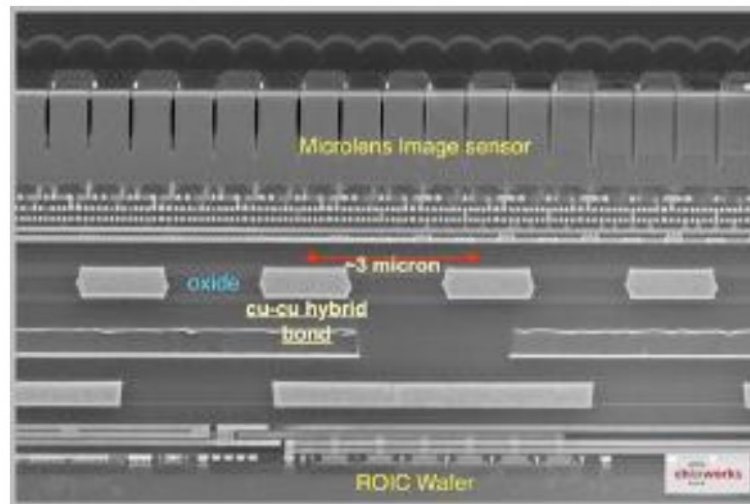
- Substrate current pulses for bias voltages from 250 (brown) to 405 (red) volts showing the onset of gain.
- Rise time of the top electrodes will be determined by the details of the CMOS well capacitance

Project Deliverables

- Design and manufacture sensors using SkyWater's 90 nm CMOS process
- Create a HEP specific MPW run
 - Reticle divided into dies of varying designs: 1/2 wafer with only sensors and 1/2 wafer with sensors & readout circuits
 - Perform detailed characterization of MAPS, LGAD, and SPAD detectors, and quantify their performance for HEP
- Enable US-teams to lead the design and fabrication of tracking detector(s) for a future Higgs factory
 - **Broad participation of university groups** in cutting edge instrumentation

3D-integrated sensors project

- Development of low-power, highly granular detectors in (\vec{x}, t)
 - Required to achieve breakthroughs across HEP, NP, BES, and FES
 - Adoption of 3D-integration has been cost-prohibitive in academia
- Supported by DOE “Accelerated Innovation in Emerging Technologies”
 - Joint development effort of SLAC and FNAL teams
 - Partner with industry leaders to implement new technologies
 - Design goal is to achieve position resolution $\sim 5 \mu\text{m}$, timing $\sim 5\text{-}10 \text{ ps}$



Synergies with other areas

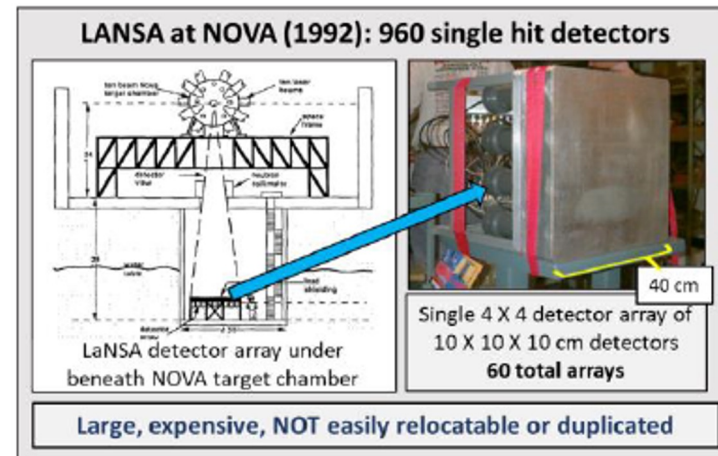
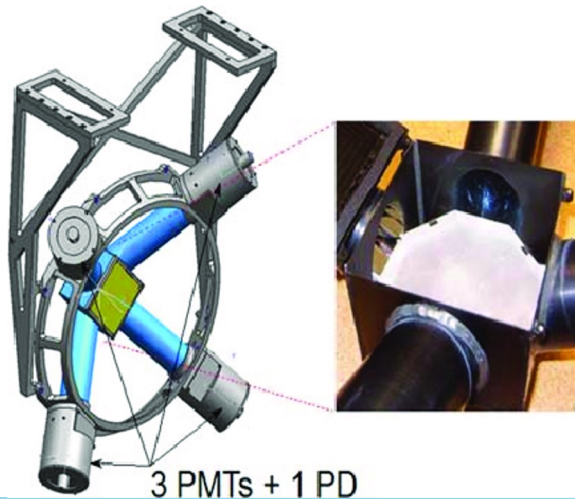
- **Designs for BES applications**

- The principal difference of applications is a requirement to also measure the deposited energy for soft X-ray imaging

- **Designs for FES applications**

- Inertial Confinement Fusion (ICF) experiments measure peak plasma burn durations below 100 ps: need to sample with precision ~ 10 ps
- X-ray imaging requires full 2D image samples over this burn history

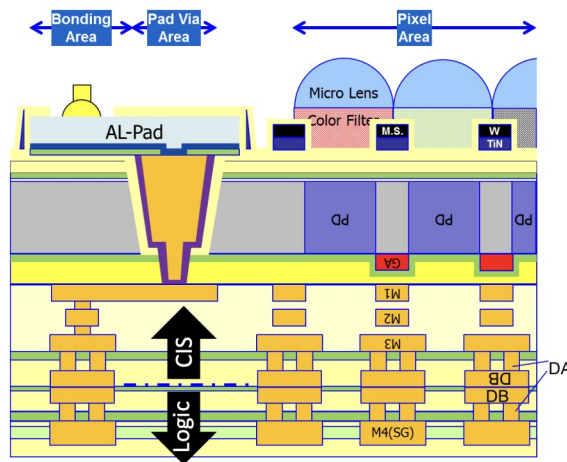
Current nTOF uses 4-PMTs



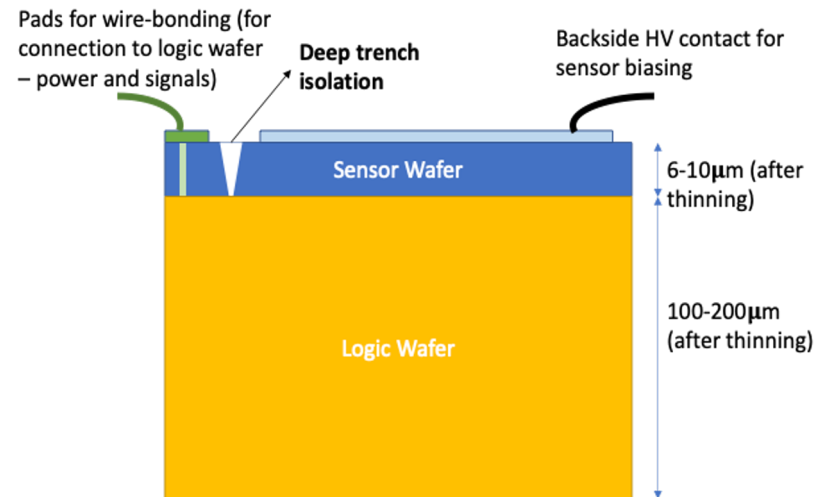
M. B. Nelson, M. D. Cable; LaNSA: A large neutron scintillator array for neutron spectroscopy at Nova. Rev. Sci. Instrum. 1 October 1992; 63 (10): 4874–4876. <https://doi.org/10.1063/1.1143536>

Development of sensors

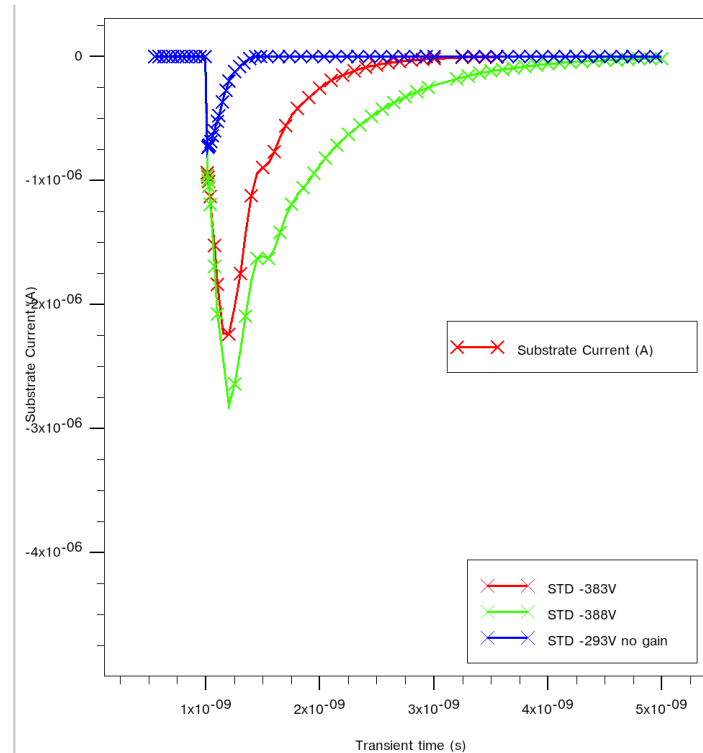
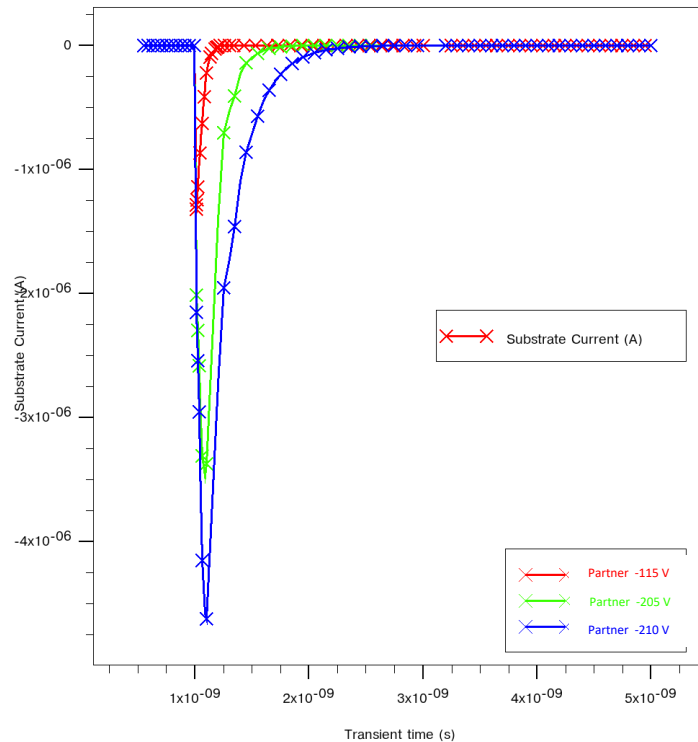
- Produce sensors on 12" wafers with a commercial partner
 - Process is a 10 μm epi; 130-150 Ohm-cm resistivity
- Simulations to study the feasibility of both gain and timing performance using vendor's parameters



Our DRM supports down to 2.5 μm pitch



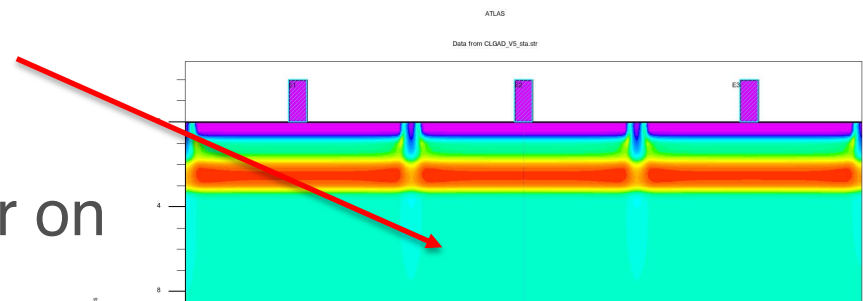
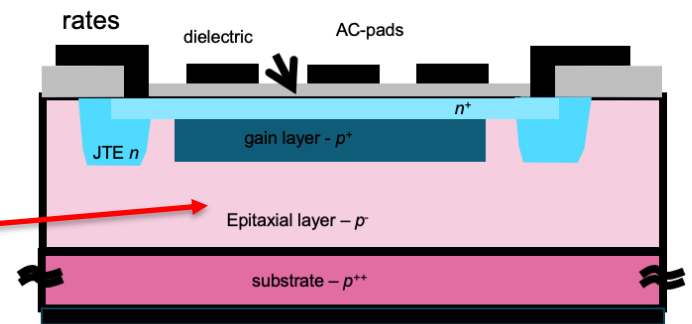
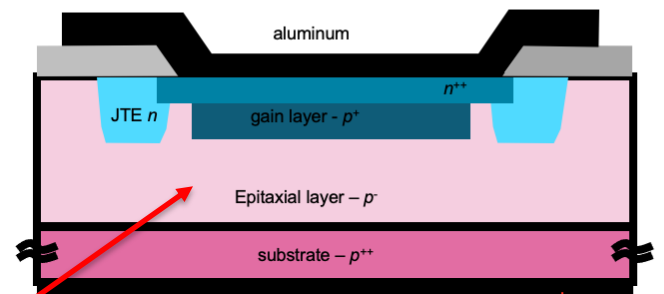
Pulse simulations



- Simulations of a “standard” LGAD and partner’s 65 nm process.
 - “Standard” process - 20 μm thick high resistivity
 - “Partner” process - 10 μm thick, moderate resistivity
- Signals from “partner” process are narrower and faster rise time

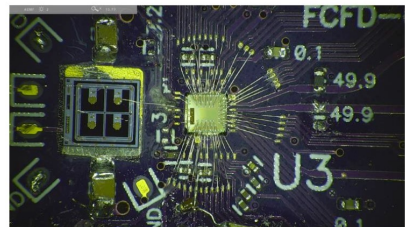
Additional processing

- The basic functionality of the device looks good with 10 μm epitaxy.
- Additional structures to be produced:
 - DC LGAD: "standard" devices
 - AC LGAD: 100% fill factor, good position resolution
 - Deep junction LGAD: for higher radiation hardness
- Working closely with our partner on the design of sensors

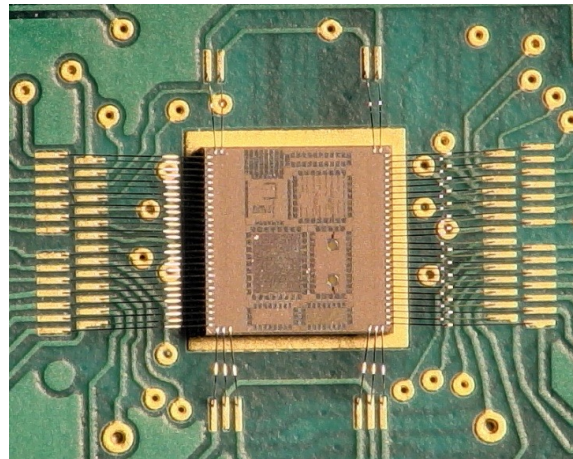


Development of ICs

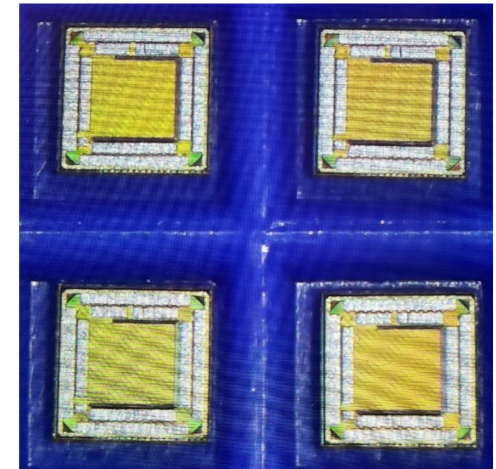
- During the 1st stage we are working to optimize and produce ASIC prototypes on MPW runs to identify the best solutions
 - **Technology**: the HEP community's choice for the future 28 nm
 - **Low Noise Amplifier**: tuned for capacitances of smaller pixels
 - **Discriminator**: Design simple and robust discriminator for low-power
 - **TDC**: dominant consumer for devices with many small pixels, need innovative solutions



[FCFDv0 pre-amp + discriminatorFCFDv0](#)



[FNAL TDC](#)



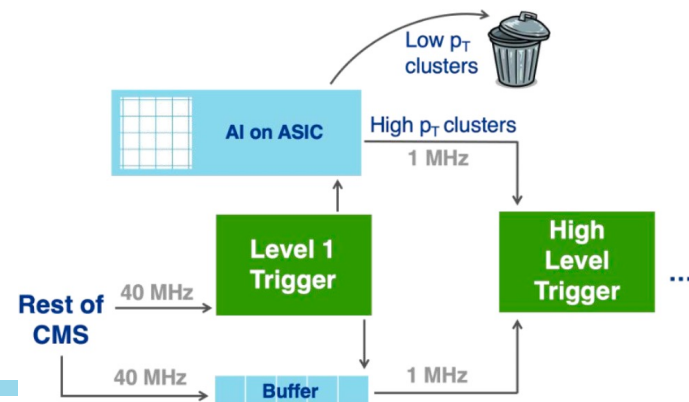
[SLAC TDC](#)



[Multi-channel FCFCv1](#)

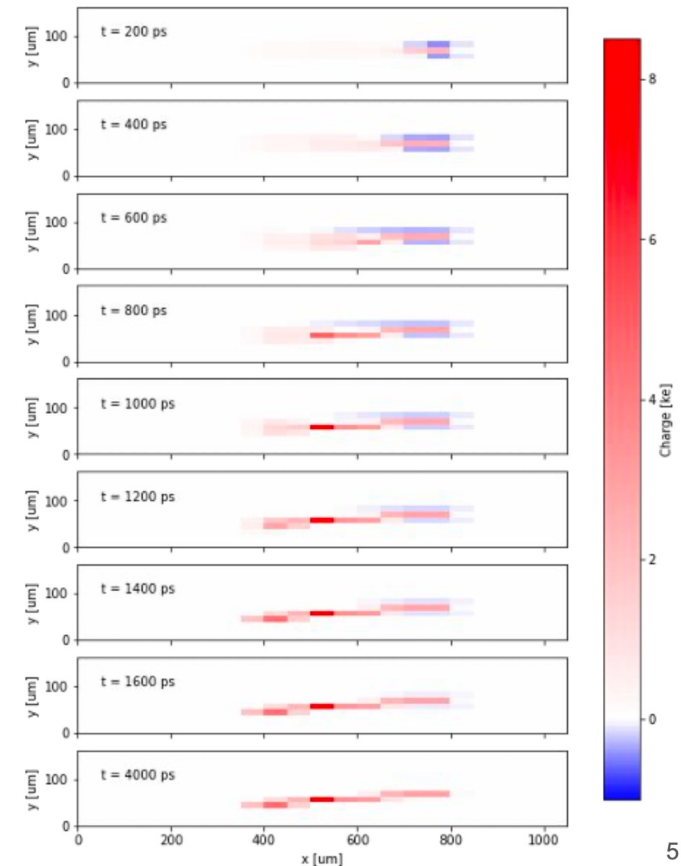
Smart Pixels project

- AI embedded on a chip to:
 - Filter data at the source to enable data reduction
 - Take advantage of pixel information to enable new physics measurements and searches
- Data reduction through
 - Filtering through removing low p_T clusters
 - Featurization through converting raw data to physics information
- Combination of approaches can reduce data rate enough to use pixel information at Level 1



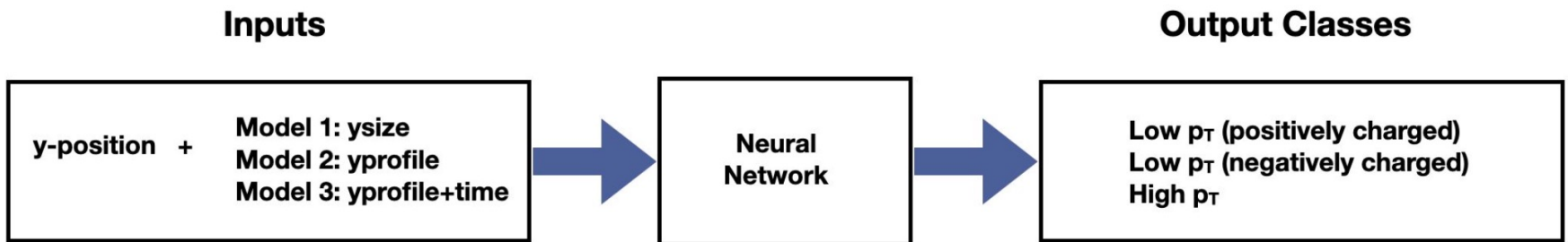
Simulation

- Simulated charge deposition from pions
- Assume a futuristic pixel detector
 - 21x13 array of pixels
 - 50x12.5 μm pitch, 100 μm thickness
 - Located at radius of 30 mm
 - 3.8 T magnetic field
 - Time steps of 200 picoseconds
- Use ML due to complicated pulse shapes, and drift & induced currents
 - y-profile is sensitive particle's p_T
 - x-profile uncorrelated with p_T

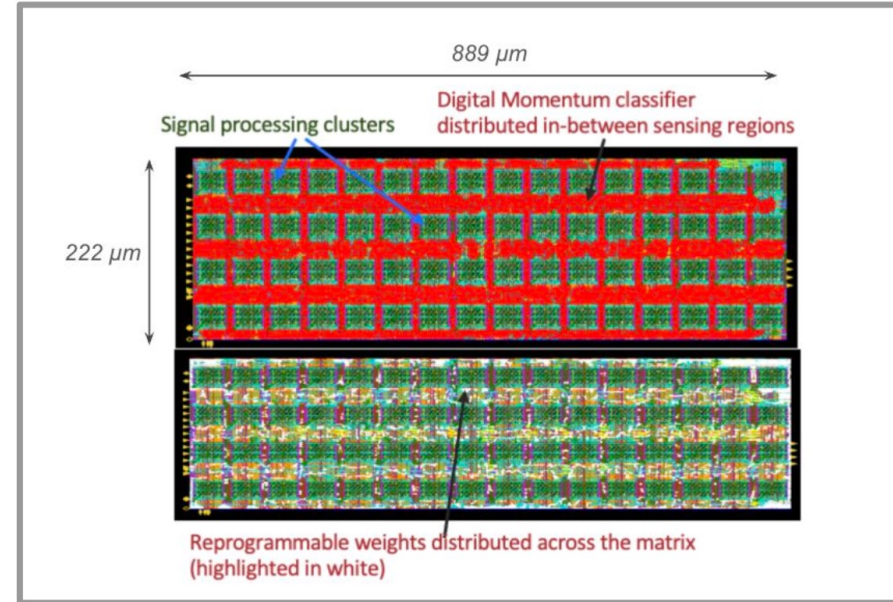
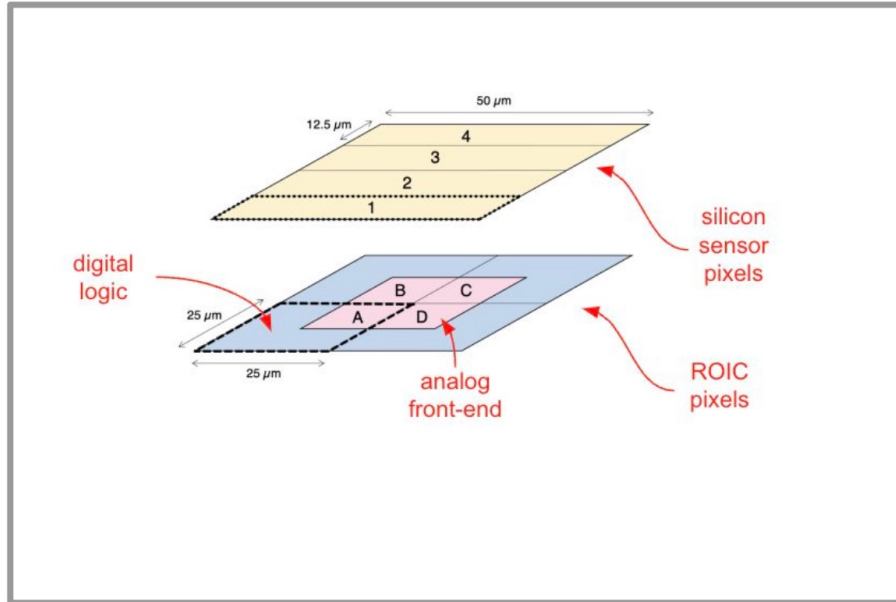


Classification

- Classification goals
 - Keep as many high p_T clusters as possible for physics
 - Decrease data bandwidth
- Region specific implementation
 - 13 locally customizable (reprogrammable weights) neural networks implemented directly in the front-end
 - Reconfigurable weights so we can adapt to changing detector conditions



ROIC implementation



- 4 analog frontends, surrounded by a digital region
- Simulation: 13 x 21; Chip: 16 x 16
- Design expected to operate at $< 300 \mu\text{W}$
- Area $< 0.2\text{mm}^2$
- The second chip has been submitted for tape out and received this spring, testing in progress

Summary

- Many exciting R&D areas that promise to enable and enrich the physics potential of the FCC-ee experiments
 - New, disruptive technologies are emerging
- Collaborative efforts are a key for the progress in many challenging directions
 - Many examples of successful collaborations presented